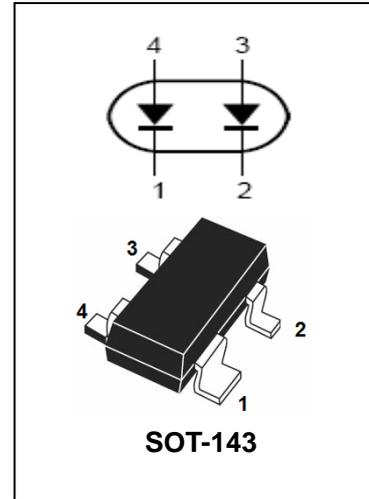


## High Voltage Double Diode

## BAW101

### FEATURES

- High Switching Speed:Max.50ns.
- High Continuous Reverse Voltage:300V.
- Electrically Insulated Diodes.



### APPLICATIONS

- High voltage switching.
- Automotive.
- Communication.

### ORDERING INFORMATION

Type No.	Marking	Package Code
BAW101	AB	SOT-143

### MAXIMUM RATING @ Ta=25°C unless otherwise specified

Characteristic	Symbol	Limits	Unit
Repetitive Peak Reverse Voltage Series connection	$V_{RRM}$	300 600	V
Continuous Reverse Voltage Series connection	$V_R$	300 600	V
Continuous Forward Current single diodes(note1) double diodes(note1)	$I_F$	250 140	mA
Repetitive Peak Forward Current	$I_{FRM}$	625	mA
Non-repetitive Peak Forward Current t=1μs	$I_{FSM}$	4.5	A
Power Dissipation(note1)	$P_d$	350	mW
Junction Temperature	$T_j$	-65 to +150	°C
Storage Temperature	$T_{STG}$	150	°C
Operating Ambient Temperature	$T_{amb}$	-65 to +150	°C

Note:1Device mounted on an FR4 Printed-circuit board,cathode-lead mounting pad=1cm<sup>2</sup>.

High Voltage Double Diode

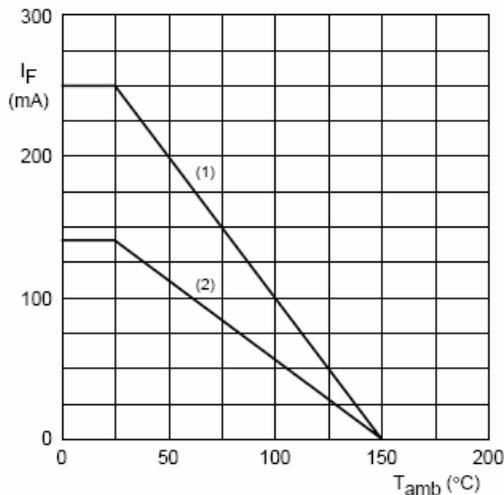
**BAW101**

**ELECTRICAL CHARACTERISTICS @ Ta=25°C unless otherwise specified**

Characteristic	Symbol	Min	Typ	MAX	UNIT	Test Condition
Reverse Breakdown Voltage	$V_{(BR)R}$	300	-	-	V	$I_R = 100\mu A$
Forward Voltage	$V_F$	-	-	1.1	V	$I_F = 100mA$ Note 1
Reverse Leakage Current	$I_R$	-	-	150 50	nA $\mu A$	$V_R = 250V$ $V_R = 250V, T_{amb} = 150^\circ C$
Diodes Capacitance	$C_d$	-	-	2	pF	$V_R = 0V, f = 1.0MHz$
Reverse Recovery Time	$t_{rr}$	-	-	50	ns	$I_F = I_R = 30mA, R_L = 100\Omega$ $I_{rr} = 0.1 * I_R$

Note: 1. Pulse tesse: pulse width=300 $\mu s$ ;  $\delta = 0.02$

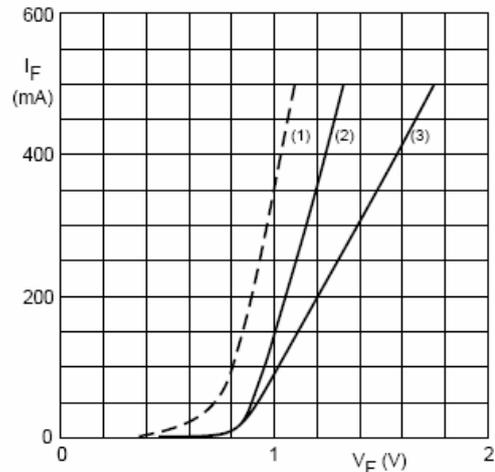
**TYPICAL CHARACTERISTICS @ Ta=25°C unless otherwise specified**



(1) Single diode loaded. (2) Double diode loaded.

Device mounted on an FR4 printed-circuit board.  
Cathode-lead mounting pad = 1 cm<sup>2</sup>.

Fig. 1 Maximum permissible continuous forward current as a function of ambient temperature.

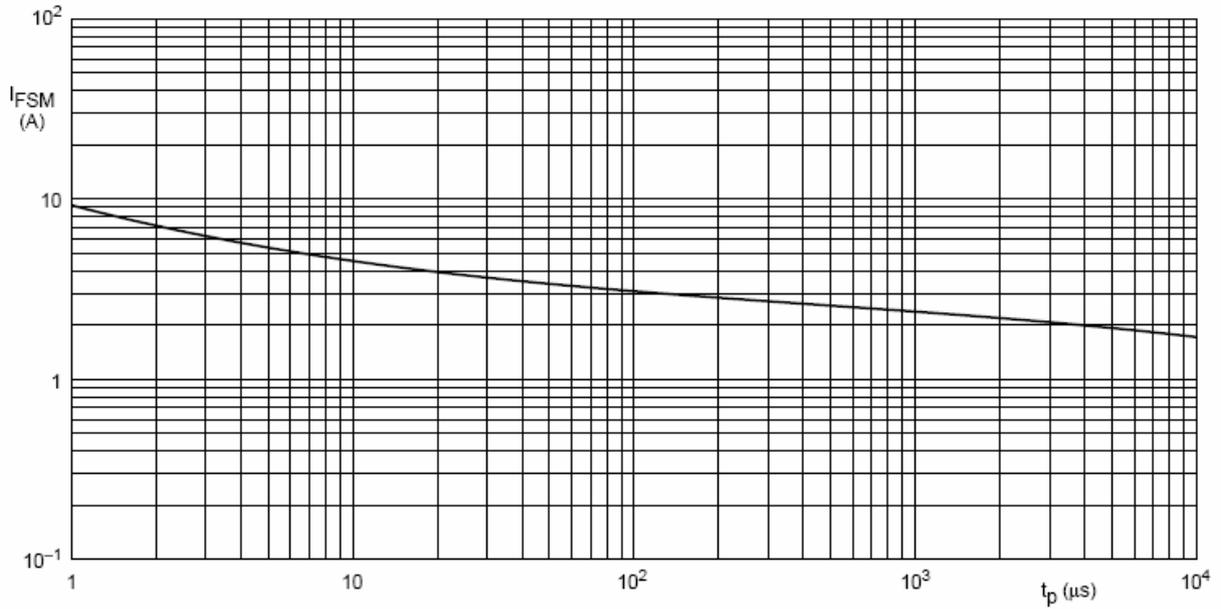


(1)  $T_j = 150^\circ C$ ; typical values.  
(2)  $T_j = 25^\circ C$ ; typical values.  
(3)  $T_j = 25^\circ C$ ; maximum values.

Fig. 2 Forward current as a function of forward voltage.

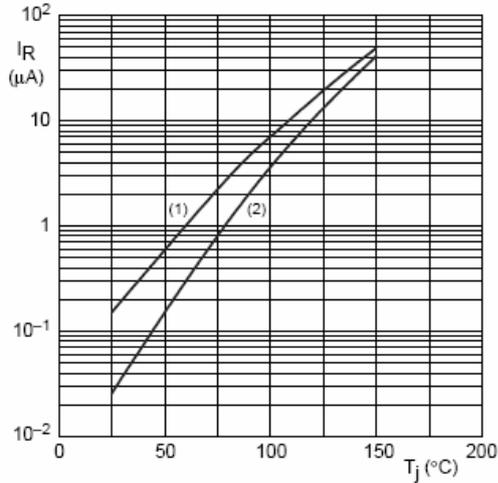
High Voltage Double Diode

**BAW101**



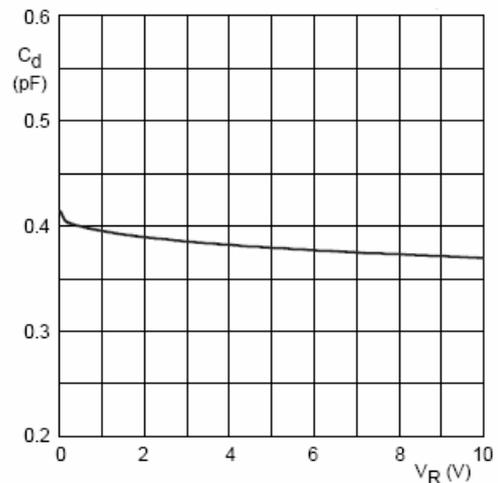
Based on square wave currents.  
 $T_j = 25$  °C prior to surge.

Fig. 3 Maximum permissible non-repetitive peak forward current as a function of pulse duration.



(1)  $V_R = V_{RMAX}$ : maximum values.  
(2)  $V_R = V_{RMAX}$ : typical values.

Fig. 4 Reverse current as a function of junction temperature.



$f = 1$  MHz;  $T_j = 25$  °C.

Fig. 5 Diode capacitance as a function of reverse voltage; typical values.

**High Voltage Double Diode**

**BAW101**

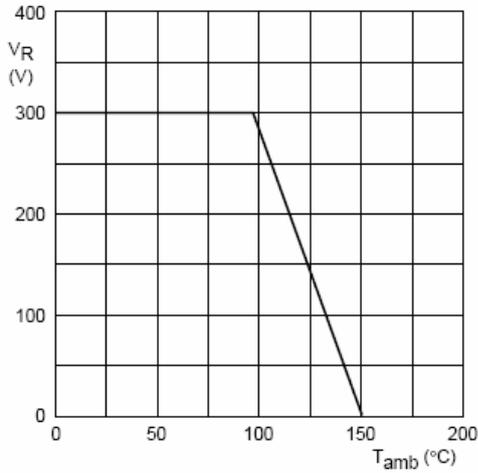
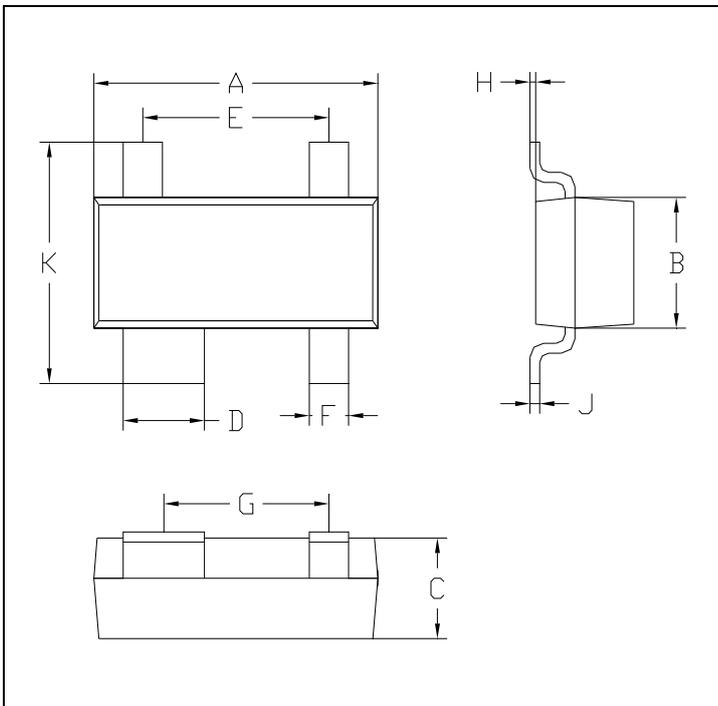


Fig.6 Maximum permissible continuous reverse voltage as a function of ambient temperature.

**PACKAGE OUTLINE**

Plastic surface mounted package

SOT-143

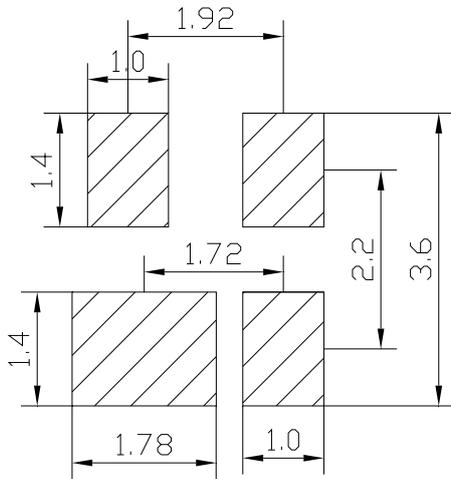


SOT-143		
Dim	Min	Max
A	2.85	2.95
B	1.20	1.40
C	1.0 Typical	
D	0.78	0.88
E	1.85	1.95
F	0.30	0.50
G	1.64	1.74
H	0.02	0.1
J	0.1 Typical	
K	2.30	2.50
All Dimensions in mm		

High Voltage Double Diode

**BAW101**

**SOLDERING FOOTPRINT**



Unit : mm

**PACKAGE INFORMATION**

Device	Package	Shipping
BAW101	SOT-143	3000/ Tape&Reel